

Amendments to th Specification

Please replace the second paragraph on page 11 as follows:

F' A spacer 28 ~~in~~ is on the sidewall of each gate stack 26. Spacers 28 are formed by subjecting a layer of silicon nitride deposited over gate stacks 26 to a spacer etch. Silicon nitride spacers 28 are generally perpendicular to silicon base layer 12. Alternatively, spacers 28 can be substantially composed of undoped silicon dioxide. As such, both spacers 28 and undoped silicon dioxide caps 52 can be made from the same materials and both act as an etch stop.

Please replace the first paragraph on page 13 as follows:

F2

Contact 34 is preferably exposed by an anisotropic plasma etch with a fluorinated chemistry that etches through BSG, PSG, BPSG, or doped silicon dioxide in general. The etch is preferably selective to undoped silicon dioxide, silicon, and silicon nitride. The fluorinated chemical etch utilizes a type of carbon fluorine gas from the group consisting of C_2F_6 , CF_4 , C_3F_8 , C_4F_{10} , C_2F_8 , CH_2F_2 , CHF_3 , C_2HF_5 , CH_3F and combinations thereof. There are other fluorinated ~~enchants~~ etchants in a substantially gas phase during the etching of the structure. An inert gas is often used in combination with the fluorinated etchant. Argon, nitrogen, and helium are examples of such an inert gas. The preferred gasses, however, are CF_4 , CH_2F_2 , CHF_3 and Ar. Alternatively CH_3F may be used in place of CH_2F_2 . In particular, the preferred ~~etchant~~ etchant is a fluorine deficient gas which is defined as a gas where there are not enough fluorine atoms to saturate the bonding for the carbon atoms.
